

MICRON.092CP4



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Stephen L. Willis ) Group Art Unit 2815  
Appl. No. : 09/552,383 / )  
Filed : April 19, 2000 / )  
For : CHEMICAL MECHANICAL )  
PLANARIZATION OF )  
CONDUCTIVE MATERIAL )  
Examiner : Jose R. Diaz )  
\_\_\_\_\_  
J. McMillon  
1/7/03

RECEIVED  
JAN - 7 2003  
TECHNOLOGY CENTER 2800

AMENDMENT AFTER FINAL

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action mailed November 4, 2002, please amend the above-captioned application as follows.

IN THE CLAIMS:

Please, amend Claims 30 and 56 as follows:

*Sub F E*  
30. (Amended) A method of forming a dielectric layer of a first thickness on a semiconductor wafer comprising:

forming the dielectric layer of the first thickness on the wafer;  
positioning a shield layer on the dielectric layer;  
positioning a sacrificial layer on the shield layer;  
depositing conductive material on the sacrificial layer;